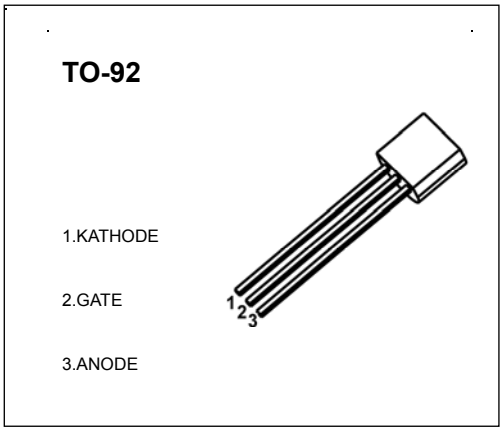
SHENZHEN HAOCHANG SEMICONDUCTOR CO.,LTD.

TO-92 Plastic-Encapsulate Thyristors



MCR 100- 6,- 8 Silicon Planar PNPN Thy ristor

MAIN FEATURES

Symbol v		alue	unit
$I_{T(RMS)}$		0.8	A
V_{DRM}	MCR100-6	400	V
	MCR100-8	600	
T_j	Junction Temperature	-40 ~ 125	℃
T_{stg}	Storage Temperature	-55 ~ 150	℃

DESCRIPTION

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

FEATURES

- Blocking voltage to 400 V (MCR100-6)
- RMS on-state current to 0.8 A
- General purpose switching

APPLICATIONS

- General purpose switching
- Phase control applications
- Solid state relays

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol		Test c onditions	Min	Max	Unit
On state voltage *	V_{TM}		I_{TM}=1A		1.7	V
Gate trigger voltage	V_{GT}		V_{AK}=7V		0.8	V
Peak Repetitive forward blocking voltage MCR10 0-6	V_{DRM}		I_{DRM}= 10 μA	400		V
MCR100-8				600		
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}		V_{AK}= Rated V_{DRM} or V_{RRM}		10	μA
Holding current	I_H		I_{HL}=20mA ,V_{AK} =7V		5	mA
Gate trigger current	I_{GT}	A2	V_{AK}=7V	5	15	μA
		A1		15	30	μA
		A		30	80	μA
		B		80	200	μA

* Forward current applied for 1 ms maximum duration，duty cycle≤1%。

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